

HIGH EFFICIENCY POWER RECTIFIER

DESCRIPTION: 1200 VOLT, 2.0 AMP ULTRA FAST RECTIFIER

FEATURES:

- Single Chip Construction
- Hermetically Sealed
- Metallurgically Bonded
- Ultra Fast Recovery: 60 ns max @ 25°C
- Low Reverse Leakage Current
- For High Efficiency Applications
- TX, TXV and S-Level Screening Available

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^\circ\text{C}$ unless otherwise specified

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	-	1200	Vdc
Average DC Output Current (I_o)	$T_L = +75^\circ\text{C}$, $L = 0''$	-	-	2.0	Amps
Peak Single Cycle Surge Current (I_{FSM})	$t_p = 8.3$ ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	60	Amps(pk)
Operating and Storage Temp. (T_{OP} & T_{STG})	-	-65	-	+175	$^\circ\text{C}$
Breakdown Voltage (V_{BR})	$I_R = 50 \mu\text{A}$	1200			Vdc
Maximum Forward Voltage (V_F)	$I_F = 1.4$ A $I_F = 2.0$ A (300 μsec pulse, duty cycle < 2%)	-	-	1.6 1.95	Volts
Maximum Instantaneous Reverse Current At Rated PIV	$T_A = +25^\circ\text{C}$ $T_A = +150^\circ\text{C}$	-	-	4 600	μAmps
Reverse Recovery Time (t_{rr})	$I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$ $T_A = 25^\circ\text{C}$ $T_A = 125^\circ\text{C}$	-	-	60 200	nsec
Thermal Resistance ($R_{\theta JL}$, AXIAL) ($R_{\theta JEC}$, MELF)	Junction to Lead, $d = 0.375''$ Junction to End Caps	-	-	22 6.5	$^\circ\text{C/W}$

SENSITRON

SEMICONDUCTOR

SRS3120HE
SRS3120HEU

TECHNICAL DATA
DATA SHEET 5141, REV -

MECHANICAL DIMENSIONS In Inches / (mm), min./max.

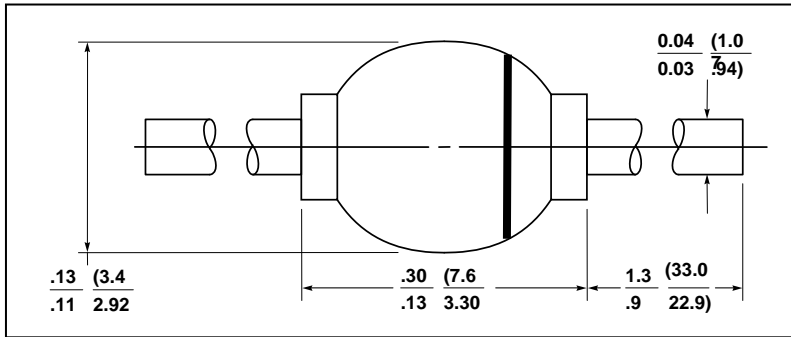
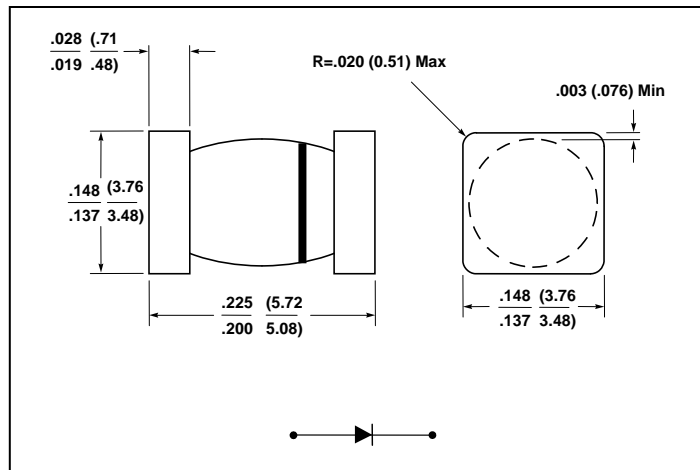


FIG. 306: Axial Lead Rectifier Outlines



MELF-B: MELF Package Outlines

NOTE: Cathode side of device is indicated by dark band marked on body.

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